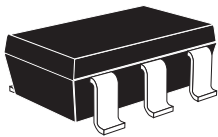


ZXMN6A08E6

60V N-CHANNEL ENHANCEMENT MODE MOSFET

SUMMARY

$V_{(BR)DSS}$	$R_{DS(on)}$ (Ω)	I_D (A)
60	0.080 @ $V_{GS} = 10V$	3.5
	0.150 @ $V_{GS} = 4.5V$	2.5



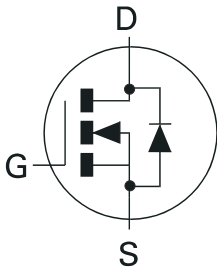
SOT23-6

DESCRIPTION

This new generation trench MOSFET from Zetex features a unique structure combining the benefits of low on-resistance and fast switching, making it ideal for high efficiency power management applications.

FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- SOT23-6 package

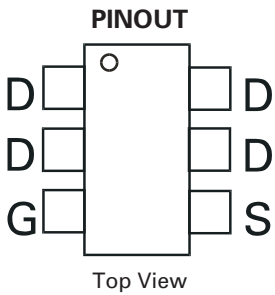


APPLICATIONS

- DC - DC converters
- Power management functions
- Disconnect switches
- Motor control

ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXMN6A08E6TA	7"	8mm	3000 units
ZXMN6A08E6TC	13"	8mm	10000 units



DEVICE MARKING

- 6A8

ZXMN6A08E6

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DSS}	60	V
Gate Source Voltage	V_{GS}	± 20	V
Continuous Drain Current $V_{GS}=10V$; $T_A=25^\circ C$ (b) $V_{GS}=10V$; $T_A=70^\circ C$ (b) $V_{GS}=10V$; $T_A=25^\circ C$ (a)	I_D	3.5 2.8 2.8	A
Pulsed Drain Current (c)	I_{DM}	16	A
Continuous Source Current (Body Diode) (b)	I_S	2.6	A
Pulsed Source Current (Body Diode) (c)	I_{SM}	16	A
Power Dissipation at $T_A=25^\circ C$ (a) Linear Derating Factor	P_D	1.1 8.8	W mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ (b) Linear Derating Factor	P_D	1.7 13.6	W mW/ $^\circ C$
Operating and Storage Temperature Range	$T_j:T_{stg}$	-55 to +150	$^\circ C$

THERMAL RESISTANCE

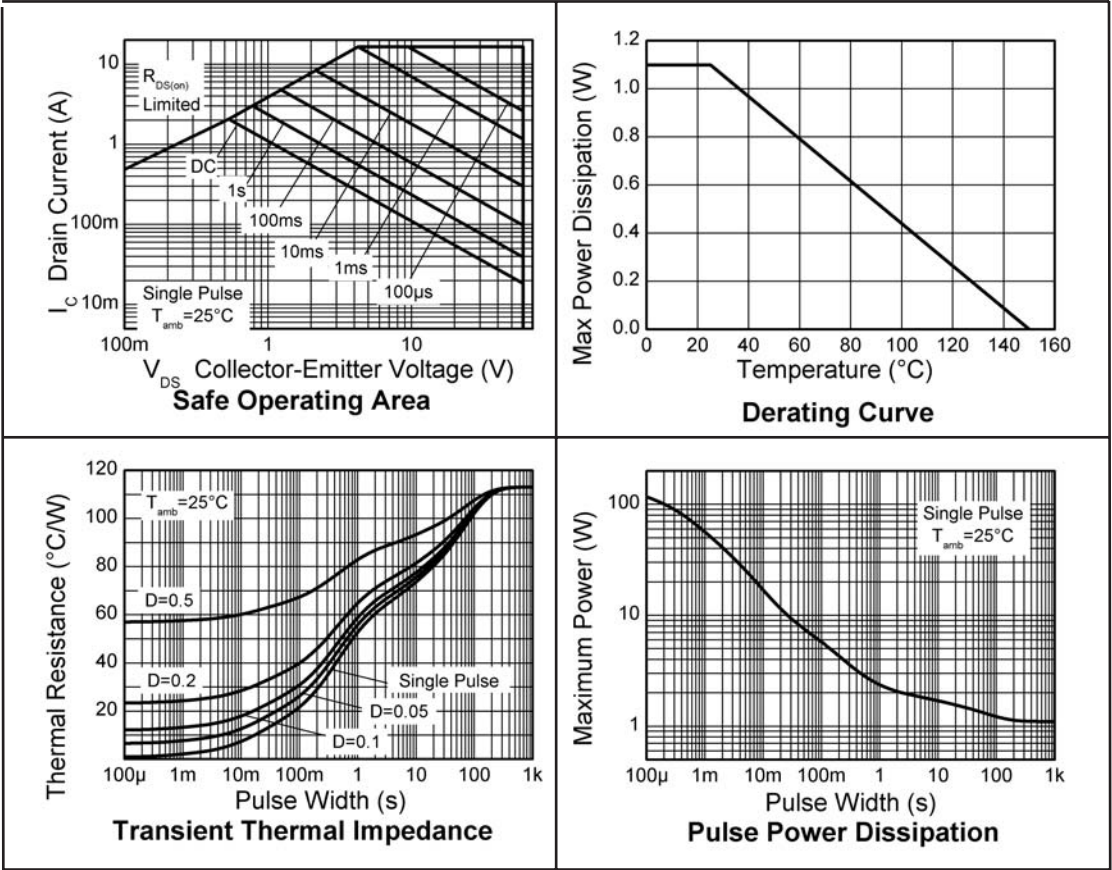
PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	$R_{\theta JA}$	113	$^\circ C/W$
Junction to Ambient (b)	$R_{\theta JA}$	73	$^\circ C/W$

NOTES

- (a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions
(b) For a device surface mounted on FR4 PCB measured at $t \leq 10$ secs.
(c) Repetitive rating 25mm x 25mm FR4 PCB, $D = 0.02$, pulse width 300 μs - pulse width limited by maximum junction temperature.

ZXMN6A08E6

CHARACTERISTICS



ZXMN6A08E6

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

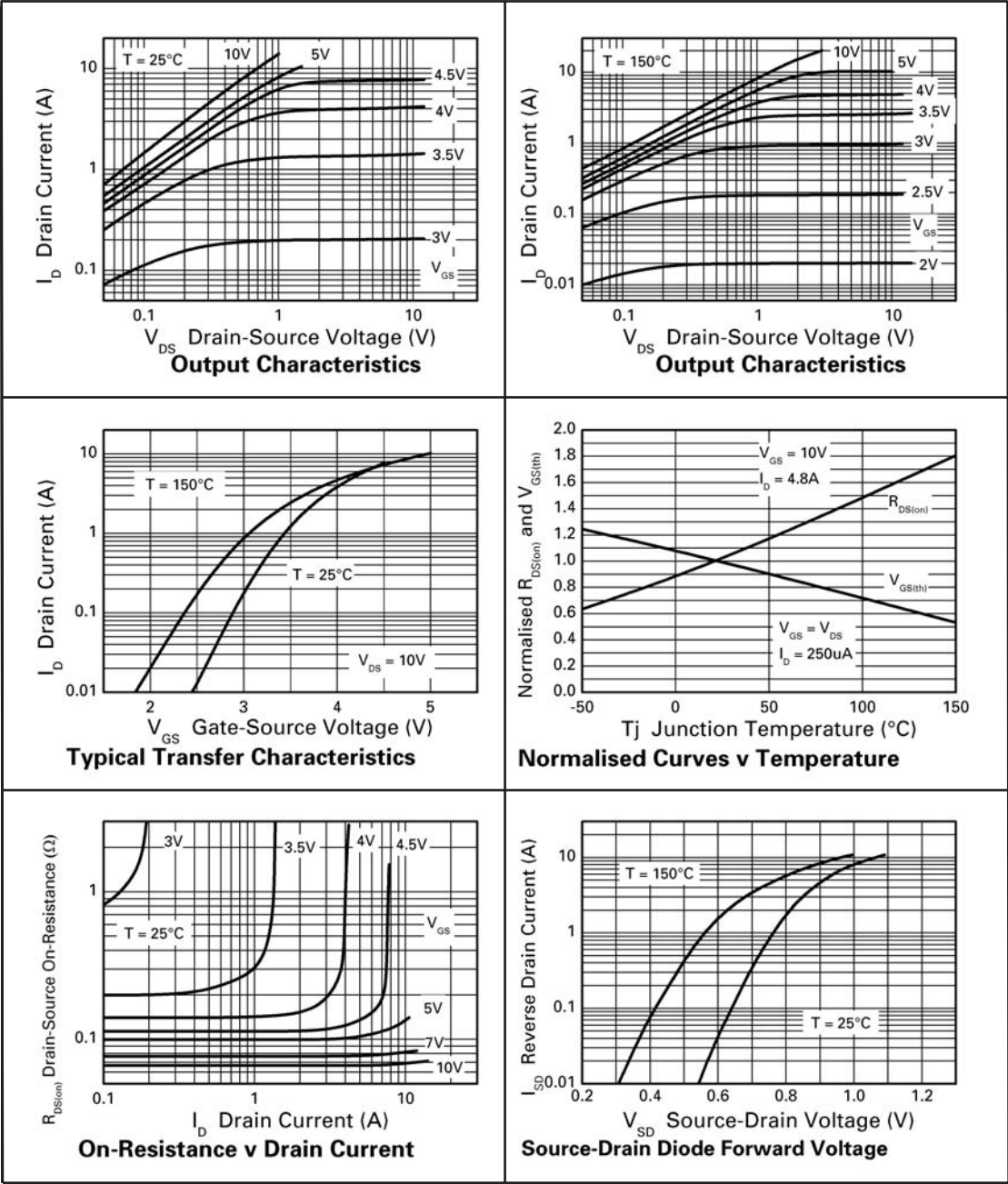
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
STATIC						
Drain-Source Breakdown Voltage	V(BR)DSS	60			V	I _D =250μA, V _{GS} =0V
Zero Gate Voltage Drain Current	I _{DSS}			0.5	μA	V _{DS} =60V, V _{GS} =0V
Gate-Body Leakage	I _{GSS}			100	nA	V _{GS} =±20V, V _{DS} =0V
Gate-Source Threshold Voltage	V _{GS(th)}	1			V	I _D =250μA, V _{DS} = V _{GS}
Static Drain-Source On-State Resistance (1)	R _{DS(on)}			0.080 0.150	Ω Ω	V _{GS} =10V, I _D =4.8A V _{GS} =4.5V, I _D =4.2A
Forward Transconductance (1)(3)	g _{fs}		6.6		S	V _{DS} =15V,I _D =4.8A
DYNAMIC (3)						
Input Capacitance	C _{iss}		459		pF	V _{DS} =40 V, V _{GS} =0V, f=1MHz
Output Capacitance	C _{oss}		44.2		pF	
Reverse Transfer Capacitance	C _{rss}		24.1		pF	
SWITCHING(2) (3)						
Turn-On Delay Time	t _{d(on)}		2.6		ns	V _{DD} =30V, I _D =1.5A R _G ≐6.0Ω, V _{GS} =10V
Rise Time	t _r		2.1		ns	
Turn-Off Delay Time	t _{d(off)}		12.3		ns	
Fall Time	t _f		4.6		ns	
Gate Charge	Q _g		4.0		nC	V _{DS} =30V,V _{GS} =5V, I _D =1.4A
Total Gate Charge	Q _g		5.8		nC	V _{DS} =30V,V _{GS} =10V, I _D =1.4A
Gate-Source Charge	Q _{gs}		1.4		nC	
Gate-Drain Charge	Q _{gd}		1.9		nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	V _{SD}		0.88	1.2	V	T _J =25°C, I _S =4A, V _{GS} =0V
Reverse Recovery Time (3)	t _{rr}		19.2		ns	T _J =25°C, I _S =1.4A, di/dt= 100A/μs
Reverse Recovery Charge (3)	Q _{rr}		30.3		nC	

NOTES

- (1) Measured under pulsed conditions. Pulse width=300 μs ; duty cycle $\leq 2\%$.
 (2) Switching characteristics are independent of operating junction temperature.
 (3) For design aid only, not subject to production testing.

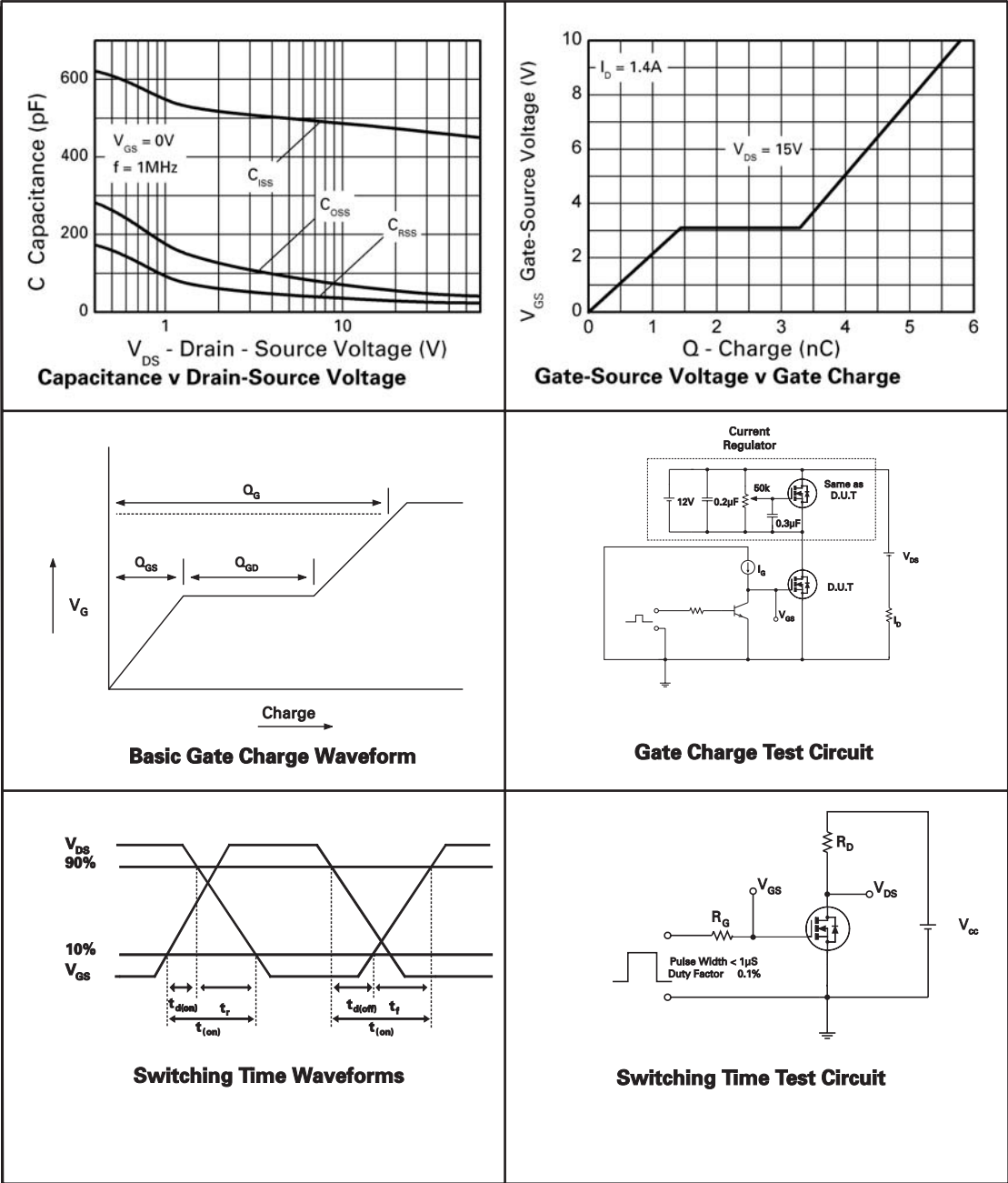
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TYPICAL CHARACTERISTICS



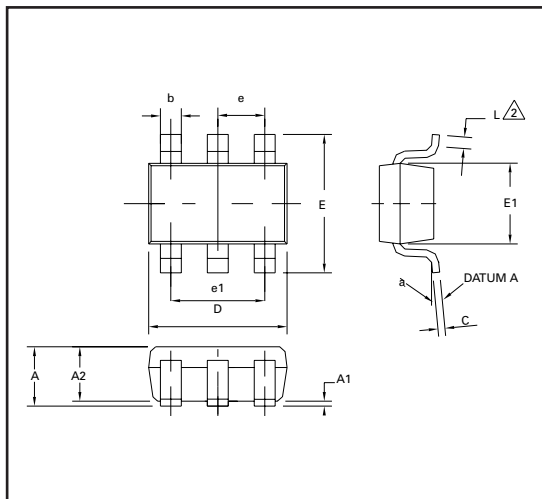
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TYPICAL CHARACTERISTICS

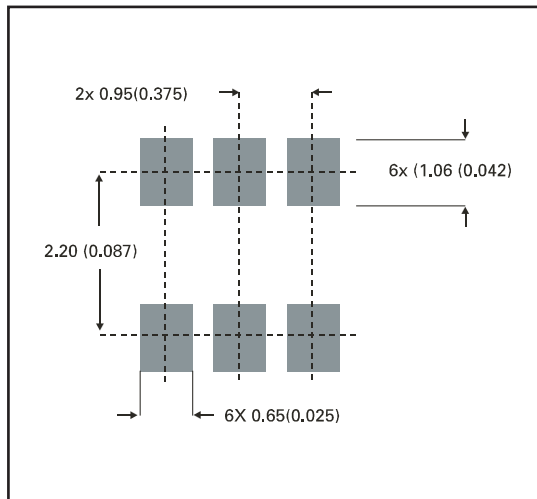


ZXMN6A08E6

PACKAGE OUTLINE



PAD LAYOUT DETAILS



CONTROLLING DIMENSIONS IN MILLIMETERS APPROX CONVERSIONS INCHES.

PACKAGE DIMENSIONS

DIM	Millimetres		Inches		DIM	Millimetres		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	0.90	1.45	0.35	0.057	E	2.60	3.00	0.102	0.118
A1	0.00	0.15	0	0.006	E1	1.50	1.75	0.059	0.069
A2	0.90	1.30	0.035	0.051	L	0.10	0.60	0.004	0.002
b	0.35	0.50	0.014	0.019	e	0.95 REF		0.037 REF	
C	0.09	0.20	0.0035	0.008	e1	1.90 REF		0.074 REF	
D	2.80	3.00	0.110	0.118	L	0°	10°	0°	10°

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ISSUE 4 - MAY 2006